Silicon NPN Power Transistors 3DD200

DESCRIPTION

- With TO-3 package
- High collector-base breakdown voltage
  : V_{CBO}=250V

APPLICATIONS

- For TV horizontal output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	250	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
P_C	Collector power dissipation	T_C=75℃	30	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	CHARACTERISTICS	MAX	UNIT
R θ jc	Thermal resistance junction to case	1.5	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA ;I_B=0	100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ;I_E=0	250			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A; I_B=0.3A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A; I_B=0.3A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=250V; I_E=0			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=2A ; V_{CE}=5V	30		120	
t_f	Fall time	I_C=3A; I_{B1}=0.2A; I_{B2}=-0.3A			1	μs

PACKAGE OUTLINE

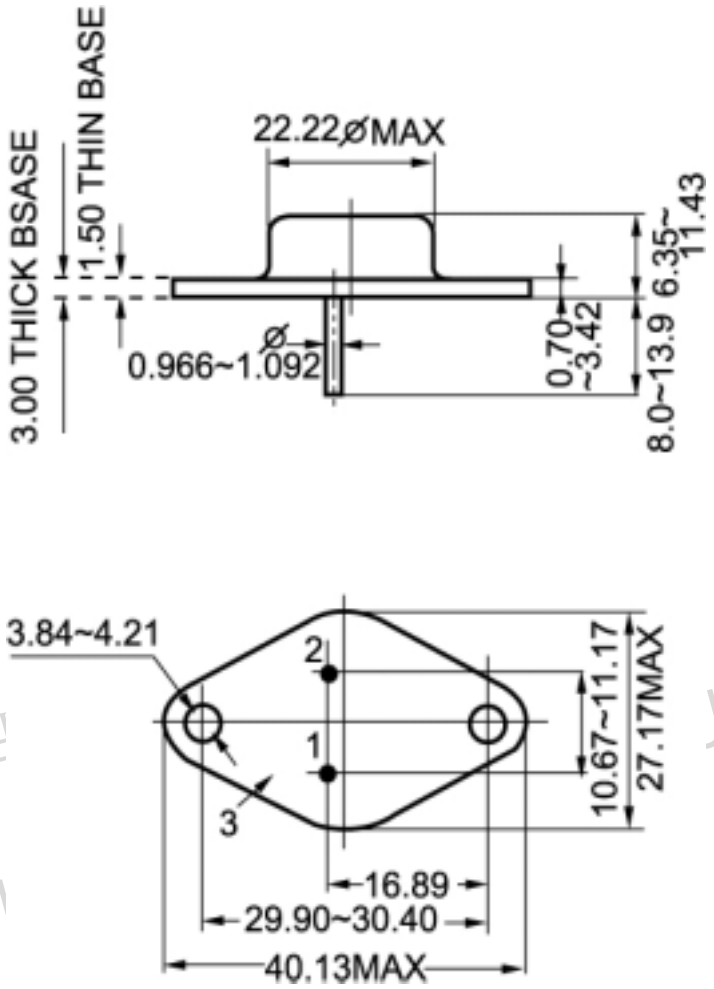

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)